

### FEATURES

- Double Side Cooling
- High Surge Capability

### APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	Conditions
DCR2400B85	8500	$T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 300\text{mA}$ , $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ , $V_{DSM} \text{ \& } V_{RSM} =$ $V_{DRM} \text{ \& } V_{RRM} + 100\text{V}$ respectively
DCR2400B80	8000	
DCR2400B75	7500	
DCR2400B70	7000	

Lower voltage grades available.

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR2400B85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### KEY PARAMETERS

$V_{DRM}$	8500V
$I_{T(AV)}$	2370A
$I_{TSM}$	32500A
$dV/dt^*$	1500V/ $\mu\text{s}$
$dI/dt$	300A/ $\mu\text{s}$

\* Higher  $dV/dt$  selections available

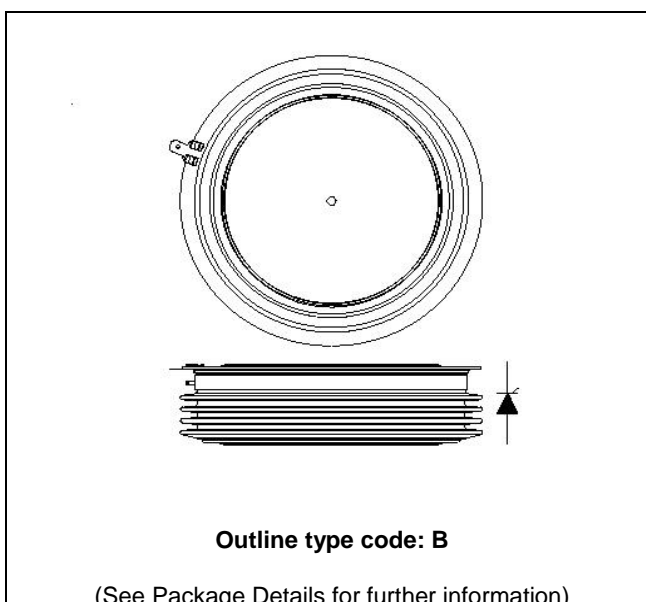


Fig. 1 Package outline

## CURRENT RATINGS

$T_{case} = 60^{\circ}C$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
<b>Double Side Cooled</b>				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	2370	A
$I_{T(RMS)}$	RMS value	-	3723	A
$I_T$	Continuous (direct) on-state current	-	3500	A

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	32.5	kA
$I^2t$	$I^2t$ for fusing	$V_R = 0$	5.28	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.007	$^{\circ}C/W$
		Single side cooled	Anode DC	-	0.0116	$^{\circ}C/W$
			Cathode DC	-	0.0181	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 76.0kN (with mounting compound)	Double side	-	0.0014	$^{\circ}C/W$
			Single side	-	0.0028	$^{\circ}C/W$
$T_{vj}$	Virtual junction temperature	On-state (conducting)		-	135	$^{\circ}C$
		Reverse (blocking)		-	125	$^{\circ}C$
$T_{stg}$	Storage temperature range			-55	125	$^{\circ}C$
$F_m$	Clamping force			68.0	84.0	kN

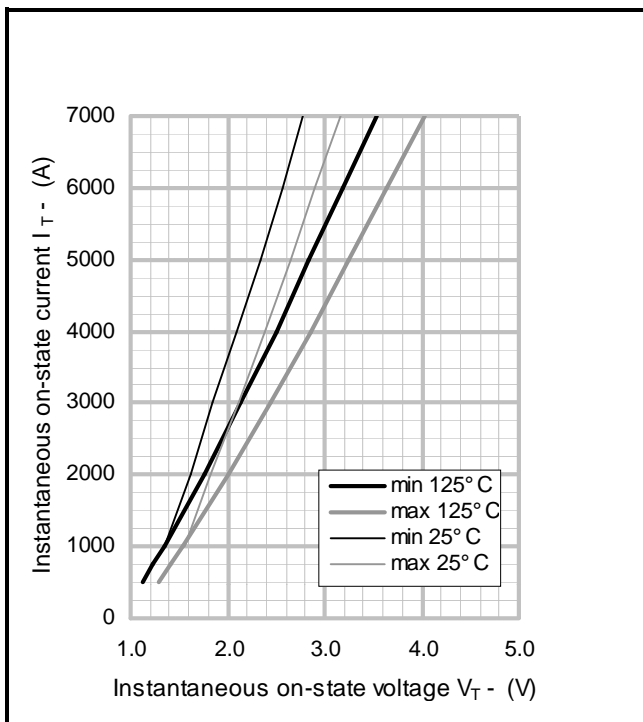
## DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125° C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125° C, gate open		-	1500	V/μs
dI/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	150	A/μs
		Gate source 30V, 10Ω, t <sub>r</sub> < 0.5μs, T <sub>j</sub> = 125° C	Non-repetitive	-	300	A/μs
V <sub>T(TO)</sub>	Threshold voltage – Low level	500 to 2400A at T <sub>case</sub> = 125° C		-	1.037	V
	Threshold voltage – High level	2400 to 72000A at T <sub>case</sub> = 125° C		-	1.229	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2400A at T <sub>case</sub> = 125° C		-	0.487	mΩ
	On-state slope resistance – High level	2400A to 72000A at T <sub>case</sub> = 125° C		-	0.398	mΩ
t <sub>gd</sub>	Delay time	V <sub>D</sub> = 67% V <sub>DRM</sub> , gate source 30V, 10Ω t <sub>r</sub> = 0.5μs, T <sub>j</sub> = 25° C		TBD	TBD	μs
t <sub>q</sub>	Turn-off time	T <sub>j</sub> = 125° C, V <sub>R</sub> = 200V, dI/dt = 1A/μs, dV <sub>DR</sub> /dt = 20V/μs linear		600	1000	μs
Q <sub>S</sub>	Stored charge	I <sub>T</sub> = 2000A, T <sub>j</sub> = 125° C, dI/dt – 1A/μs,		6000	11000	μC
I <sub>L</sub>	Latching current	T <sub>j</sub> = 25° C, V <sub>b</sub> = 5V		TBD	TBD	mA
I <sub>H</sub>	Holding current	T <sub>j</sub> = 25° C, R <sub>G-K</sub> = ∞, I <sub>TM</sub> = 500A, I <sub>T</sub> = 5A		TBD	TBD	mA

## GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
$V_{GD}$	Gate non-trigger voltage	At $V_{DRM}, T_{case} = 125^{\circ}C$	TBD	V
$I_{GT}$	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	250	mA
$I_{GD}$	Gate non-trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	TBD	mA

## CURVES



**Fig.2 Maximum & minimum on-state characteristics**

### $V_{TM}$ EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where  $A = 0.907134$   
 $B = -0.011004$   
 $C = 0.000304$   
 $D = 0.012936$

these values are valid for  $T_j = 125^{\circ}C$  for  $I_T$  500A to 7200A

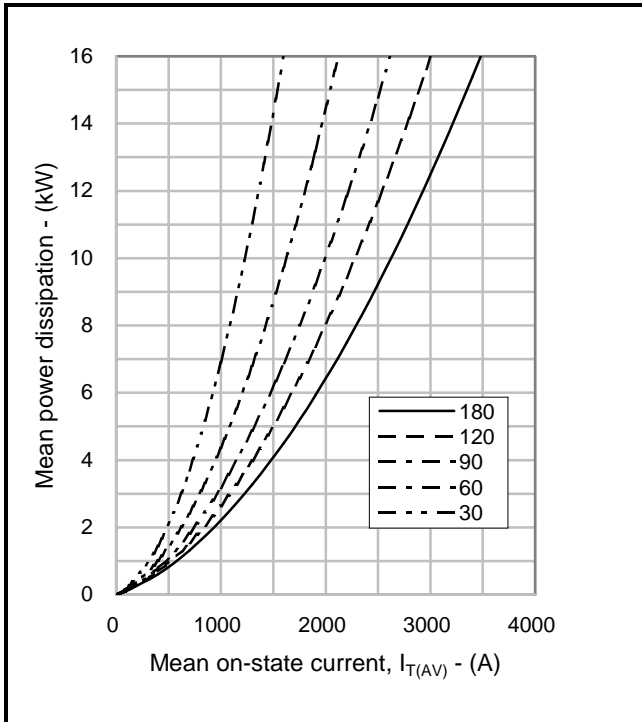


Fig.3 On-state power dissipation – sine wave

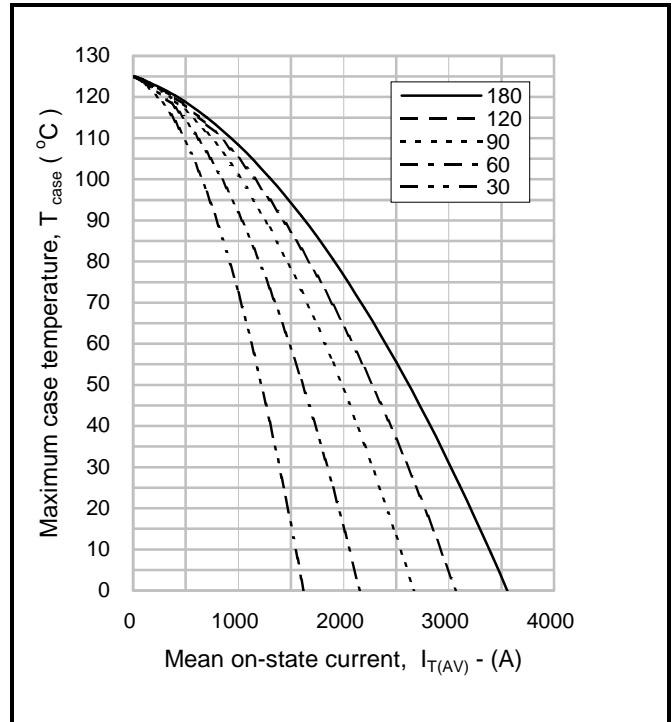


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

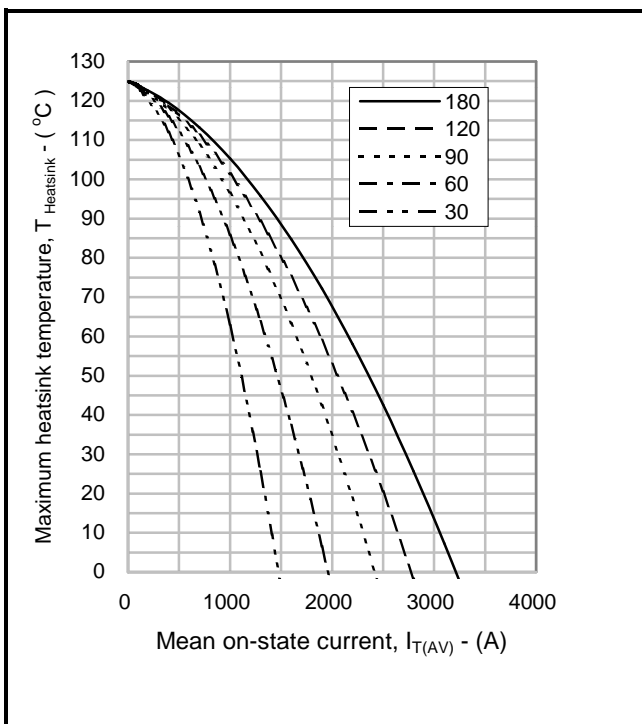


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

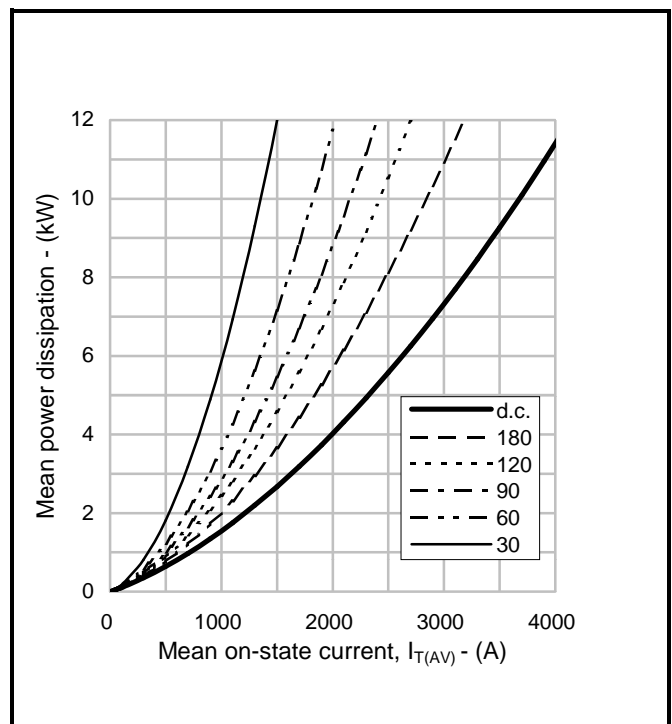
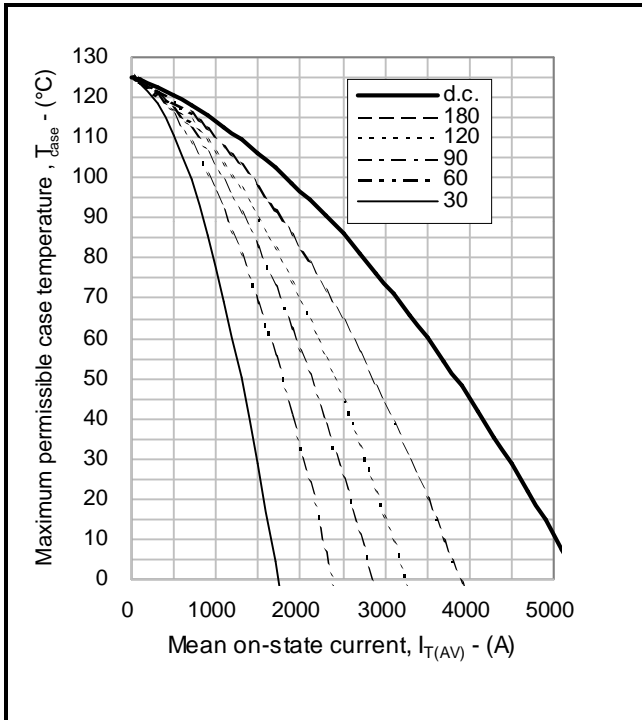
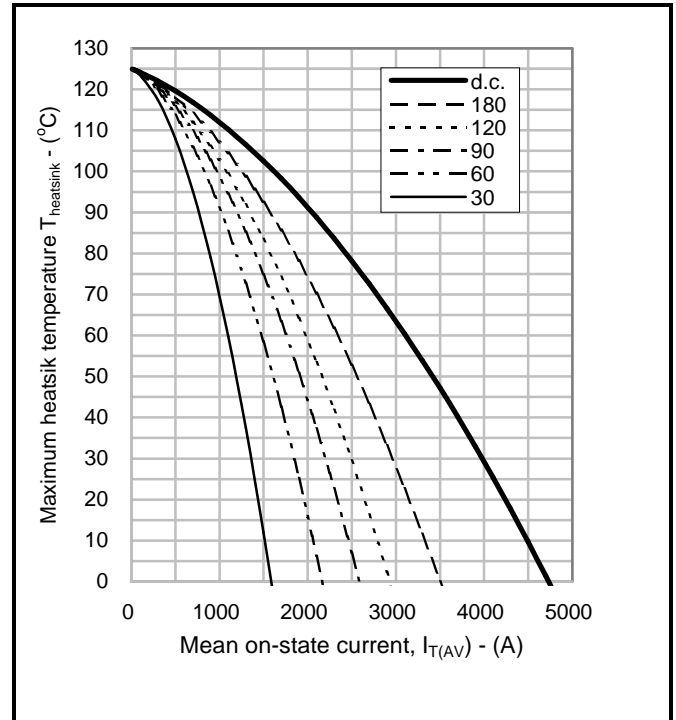


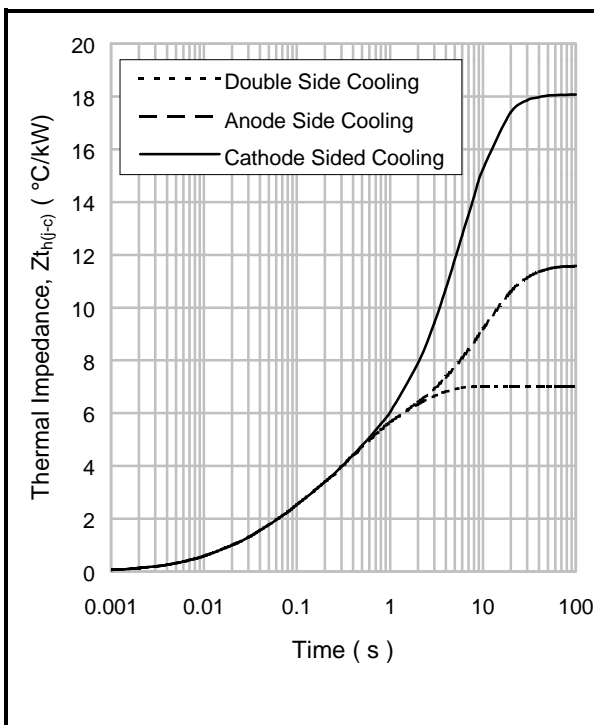
Fig.6 On-state power dissipation – rectangular wave



**Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave**



**Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave**



**Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)**

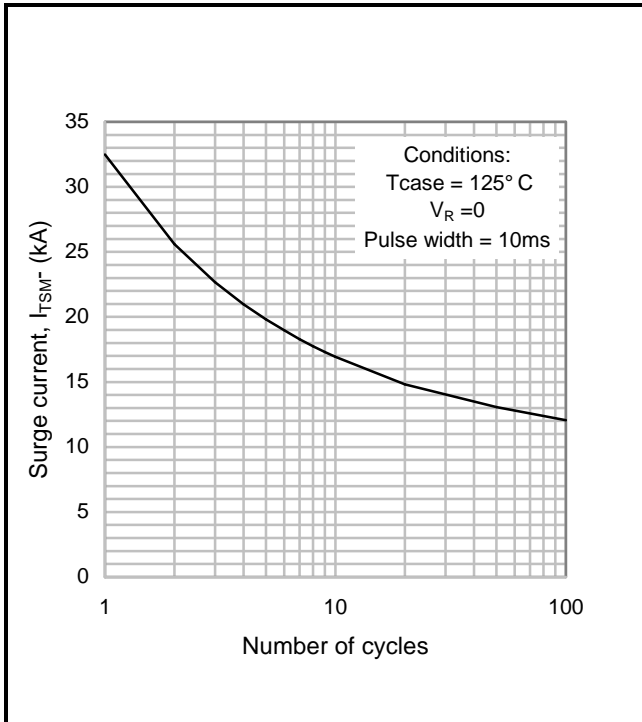
		1	2	3	4
Double side cooled	$R_{\theta}$ (°C/kW)	0.502	1.333	2.9559	2.2335
	$T_1$ (s)	0.0137081	0.0548877	0.3311925	1.6905
Anode side cooled	$R_{\theta}$ (°C/kW)	1.3035	3.138	1.1859	5.9136
	$T_1$ (s)	0.0251065	0.2410256	1.0806	11.002
Cathode side cooled	$R_{\theta}$ (°C/kW)	1.2616	2.6216	13.3603	0.8304
	$T_1$ (s)	0.0245837	0.2005035	5.7854	16.765

$$Z_{th} = \sum [R_i \times (1 - \exp. (-t/t_i))] \quad [1]$$

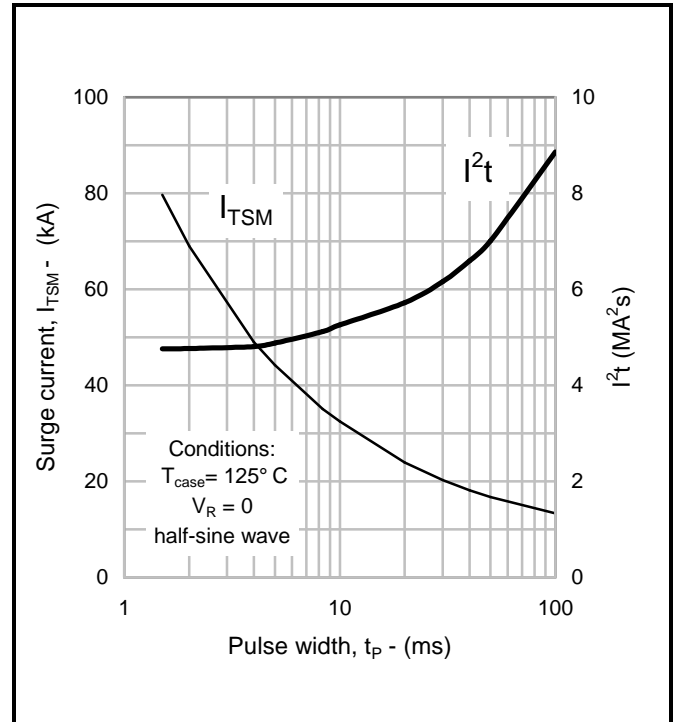
$\Delta R_{th(j-c)}$  Conduction

Tables show the increments of thermal resistance  $R_{th(j-c)}$  when the device operates at conduction angles other than d.c.

Double side cooling			Anode Side Cooling			Cathode Sided Cooling		
$\theta^\circ$	$\Delta Z_{th}(z)$		$\theta^\circ$	$\Delta Z_{th}(z)$		$\theta^\circ$	$\Delta Z_{th}(z)$	
	sine.	rect.		sine.	rect.		sine.	rect.
180	0.70	0.48	180	0.67	0.47	180	0.67	0.47
120	0.80	0.68	120	0.77	0.66	120	0.77	0.66
90	0.90	0.78	90	0.87	0.75	90	0.87	0.76
60	1.00	0.89	60	0.95	0.86	60	0.95	0.86
30	1.07	1.01	30	1.02	0.96	30	1.02	0.96
15	1.10	1.07	15	1.05	1.02	15	1.05	1.02



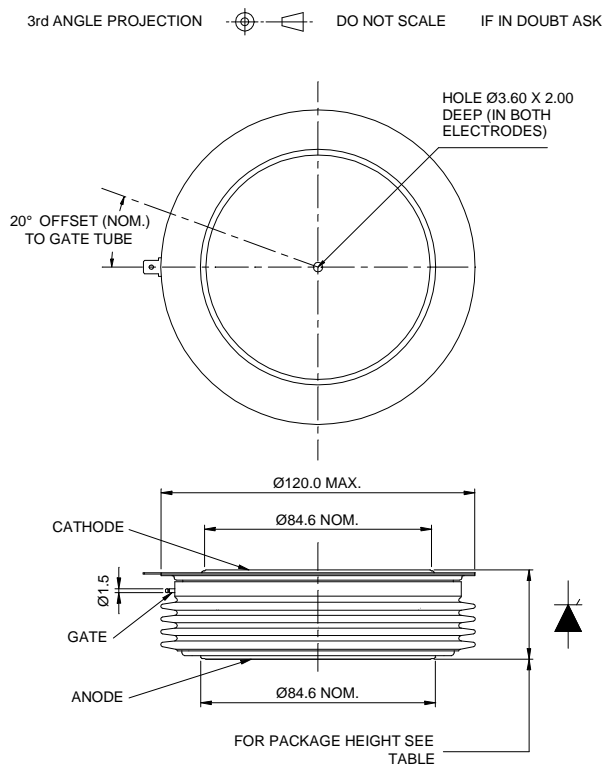
**Fig.10 Multi-cycle surge current**



**Fig.11 Single-cycle surge current**

## PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Device	Maximum Thickness (mm)	Minimum Thickness (mm)
DCR5050B22	34.565	34.115
DCR4590B28	34.64	34.19
DCR3790B42	34.87	34.42
DCR3480B52	34.99	34.54
DCR2880B65	35.25	34.8
<b>DCR2400B85</b>	<b>35.61</b>	<b>35.16</b>

Clamping force: 76kN  $\pm$ 10%  
Lead length: 420mm  
Lead terminal connector: M4 ring

**Package outline type code: B**

**Fig.15 Package outline**



## **POWER ASSEMBLY CAPABILITY**

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

## **HEATSINKS**

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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